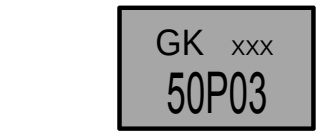
V_{DSS}	-30 V
I_D	-50 A
$R_{DS(ON)}$	8mΩ

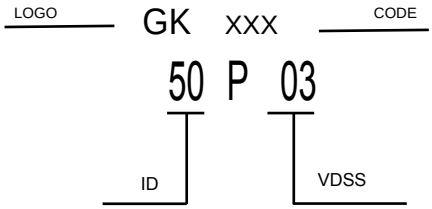
Features

- V_{DS}= -30V, I_D= -50A
  $R_{DS(ON)}$ Typ 8mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$ Typ 12mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Applications

- PWM Applications
- Load Switch
- Power Management





TO-252

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	-50	A
		T_C = 100℃	-23	A
I_{DM}	Pulsed Drain Current note1		-200	A
E_{AS}	Single Pulsed Avalanche Energy note2		121	mJ
P_D	Power Dissipation	T_C = 25℃	52	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.9	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

Electrical Characteristics (T_J=25℃unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -30V, V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -30A	-	8	10.5	mΩ
		V_{GS}= -4.5V, I_D= -20A	-	12	16	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -15V, V_{GS}=0V, f=1.0MHz	-	3564	-	pF
C_{oss}	Output Capacitance		-	416	-	pF
C_{rss}	Reverse Transfer Capacitance		-	373	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D= -20A, V_{GS}= -10V	-	37	-	nC
Q_{gs}	Gate-Source Charge		-	6.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	9.4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -15V, I_D= -30A, V_{GS}= -10V, R_{GEN}=2.5Ω	-	16	-	ns
t_r	Turn-on Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	68	-	ns
t_f	Turn-off Fall Time		-	52	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-200	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -30A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. E_{AS} condition: T_J=25℃, V_{DD}= -15V, V_G= -10V, R_G=25Ω, L=0.5mH, I_{AS}= -22A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

RATING AND CHARACTERISTIC CURVES

Figure1: Output Characteristics

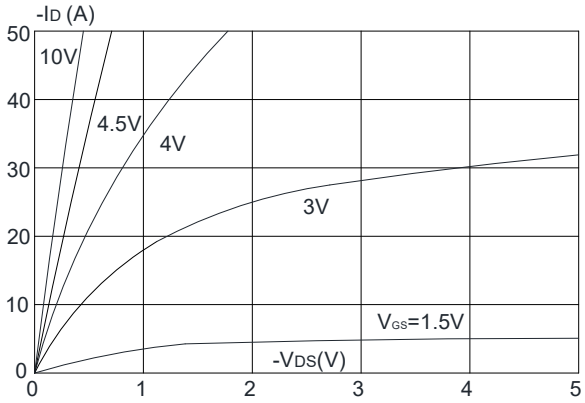


Figure 2: Typical Transfer Characteristics

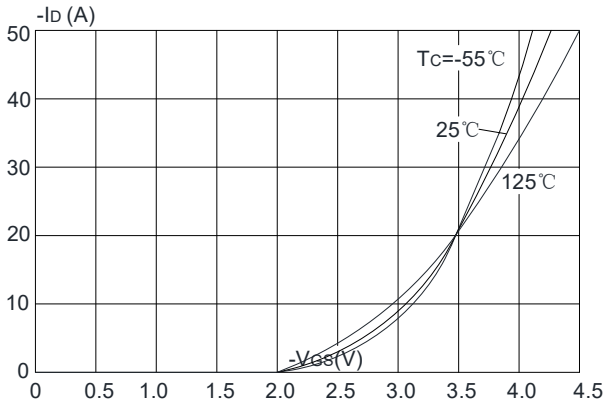


Figure 3: On-resistance vs. Drain Current

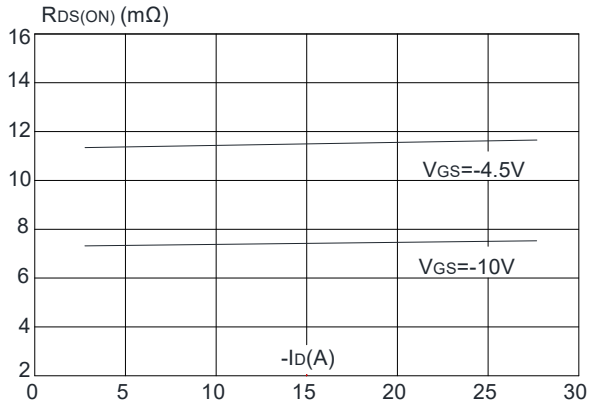


Figure 4: Body Diode Characteristics

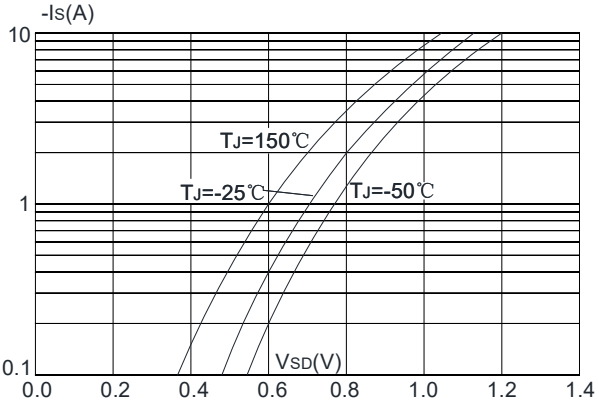


Figure 5: Gate Charge Characteristics

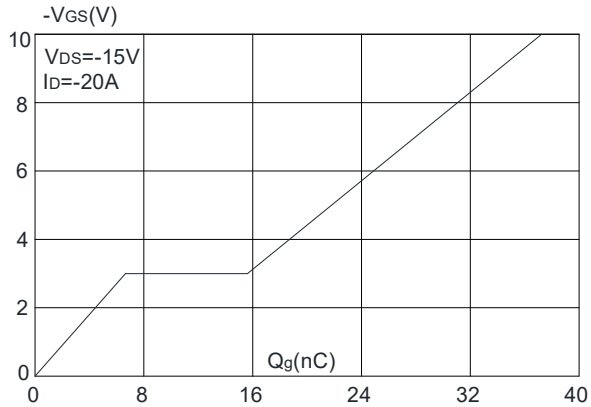
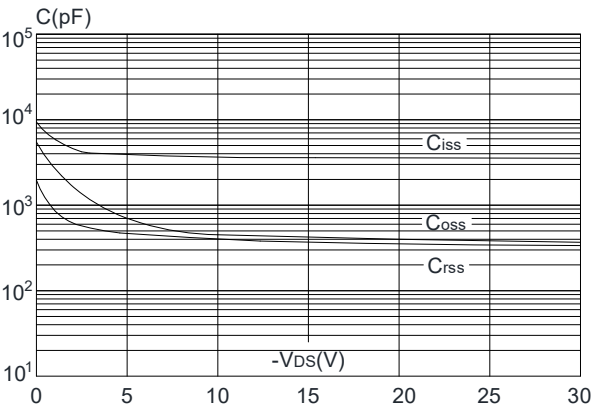


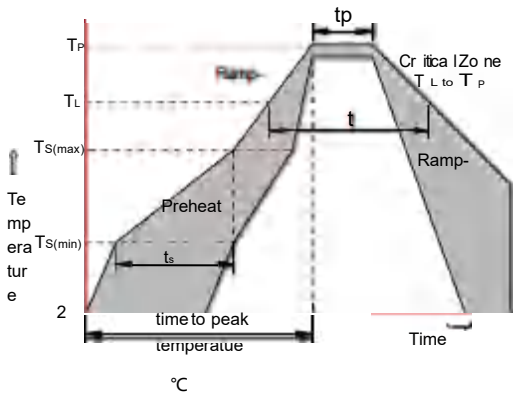
Figure 6: Capacitance Characteristics



Soldering parameters

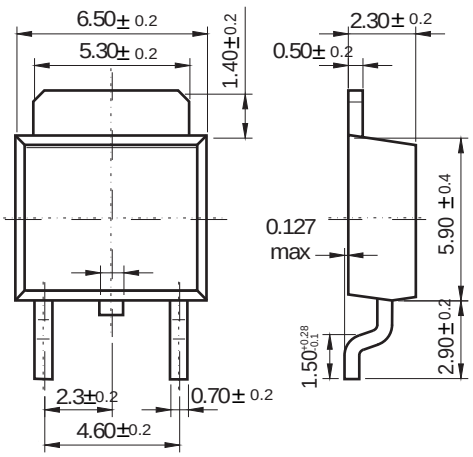
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

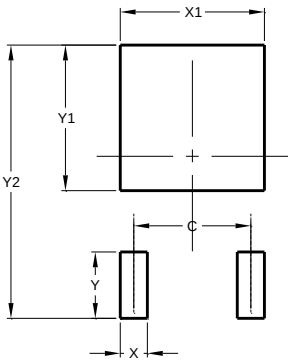


Package Dimensions & Suggested Pad Layout

TO-252



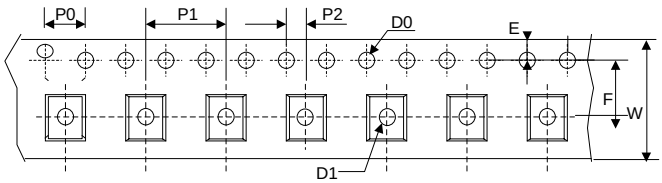
Dimensions in inches and (millimeters)

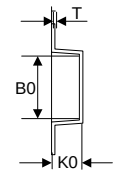


Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

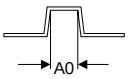
Tape & rell specification

Tape



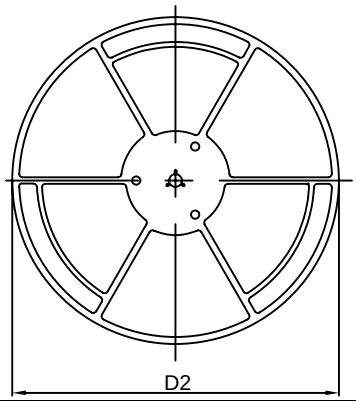


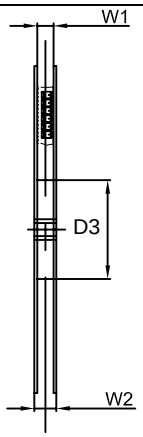
SECTION : B-B



SECTION : A-A

13” Reel





Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

Quantity: 2500PCS